SECTION 1.0  INTRODUCTION

1.1 SCOPE

This document is the Renesas Electronics America Inc. "Quality Management (QM) Plan" which is required for the QML program as defined in MIL-PRF-38535. The contents describe the operating systems and procedures used by Renesas Electronics America Inc. to meet all the requirements of the QML program. Renesas Electronics America Inc. (hereafter referred to as REA) has manufacturing operations in Palm Bay, Florida.

Renesas Electronics America Inc. is a fully certified manufacturer for Product Assurance Levels Q, V, and T.

Class T
1. Class “T” is designed for specific applications. REA does not claim Class T is the same as Class Q.
2. Reliability information is available on the REA web site: Reliability Web Site;
3. Class T RAD Hard application devices are fully tested and guaranteed to the total dose specified in the SMD drawing.
4. CLASS T TECHNOLOGIES

<table>
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</tr>
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<tbody>
<tr>
<td>AVLSI-R</td>
</tr>
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<td>P6</td>
</tr>
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</table>

1.2 AUTHORIZATION AND MAINTENANCE

The QML Plan will be maintained under configuration control. The specification may be reviewed or distributed to external customers. QML documents manually distributed externally will not be placed under change control. External customers may access the current revision of the manual via the REA web site Quality Manuals and Procedures. Revisions can be initiated by REA employees with approval by the REA Technical Review Board (TRB).

The QML Coordinator is responsible for insuring that the QM Plan is implemented and maintained to current MIL-PRF-38535 requirements.
1.3 RAD HARD PRODUCT DEVELOPMENT AND INTRODUCTION
Product design for radiation specific applications is active at this time. Product introductions of radiation hardened product will be based on characterization and formal release through DLA.
As REA introduces newly developed radiation hardened products, all necessary actions will be taken to certify the design tools, devices models and fabrication processes. Appendix C of MIL-PRF-38535 will be used as a guideline for further certification.

1.4 CONTENT
The QM Plan is documented in 4 sections and 2 appendixes
1. Introduction
2. QML General (Non Technology Specific)
3. QML Technology Specific
4. Quality Systems Reference
5. Appendix A: RAD Hard Assurance
6. Appendix B: Ship Ahead of Qualification

The format used for this plan is based on the QM plan outline in MIL-PRF-38535.

Reference is made throughout the plan to the Quality Manual for the Palm Bay operations.

Sections 2 & 4 are written general in nature. Reference is made in each of these sections to internal specifications which provide details for the operations.
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### QUALITY MANAGEMENT PLAN

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<td>QUALIFICATION TEST PLAN</td>
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### APPENDICES

- **Appendix A**: RAD HARDNESS ASSURANCE
- **Appendix B**: SHIP AHEAD OF TCI

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**Title**: QML QUALITY MANAGEMENT PLAN  
**Specification Type**: DOCS  
**Specification Number**: 999015  
**Issue**: 42  
**Page**: 4 of 80  

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SECTION 2.X  QML GENERAL (NON-TECHNOLOGY SPECIFIC)

GENERAL

Section 2.X of this manual is written to describe the general (non-technology specific) systems/requirements of the QM Plan. These systems/requirements establish the "Quality System" which is used for all product types, regardless of technology type.

SECTION 2.1  INDEX OF CERTIFIED BASELINE DOCUMENTS

GENERAL

The documentation system includes an index of specifications used in the QML program.

CONTENTS OF INDEX

The Document Control index of specifications includes; specification number, specification title and the latest revision of the specifications.

INDEX AVAILABILITY

A listing of all specification series critical to the QML program is available on-line in REA’s document control system (Intrepid).

The indexes containing specifications used to make-up the QML program will be available at the time of validation and thus will be considered the certified baseline. The complete database for the QML program resides on the electronic systems.
SECTION 2.2. CONVERSION OF CUSTOMER REQUIREMENTS

GENERAL
Conversion of customer requirements into internal process specifications utilizes the contract review system and order entry procedures. These procedures are used by Marketing and the Customer Engineering department to review the Customer Control Drawings (SCD), Statement of Work (SOW) and Purchase Orders (P.O.) and translate the customer’s requirements into internal processing procedures. These review systems are supported by Design Engineering, Product Engineering, Manufacturing Operations, Quality Assurance, Finance and Legal/Contracts, as applicable.

PROCEDURES
1. INITIAL DOCUMENT REVIEW -
The primary sources of customer requirements are the SCD, SOW, and P.O.. The Marketing Manager (MM) will initiate a Drawing Review Request (DRR) for a customer SCD or SOW. The DRR will be sent to the Customer Engineer. The SCD and SOW is compared to standard flows and, where necessary, exceptions are noted. These exceptions are negotiated between the MM/or Sale Representative and customer until acceptance is mutually achieved. Confirmations of customer acceptance to the modification are included in the permanent record file.

2. PO REVIEW AND ORDER ENTRY -
The customer generated P.O. is entered into a P.O. database. For standard flow product, the PO is sent to order entry. For custom flow product, the PO is reviewed by Customer Engineering, Engineering and Manufacturing (as required). All discrepancies are resolved and the PO is prepared for order entry.

3. CONTRACT REVIEW
The contract review system ensures:
   a. The contract has been reviewed
   b. There is a method to verify that all requirements are met.
   c. There are provisions for processing contract changes
   d. There is a method to prepare internal specifications which reflect customer requirements.

QUALITY SUPPORT DOCUMENTS
240114 Customer Documentation Review and Specification Generation
999053 Intrepid Application
999032 Ship Ahead of Qual Instructions and Non-Std Product Option Descriptions (R/S Specs)
999003 Contract Review Procedures for Sales
999017 Part Number and Structure Definition
SECTION 2.2.1 DEVICE SPECIFICATION REQUIREMENTS

GENERAL
Device specifications are written for all products to reflect the requirements of MIL-PRF-38535. These device specifications are either controlled by Defense Logistics Agency Land and Maritime (DLA) or are part of the REA internal document control program.

DEVICE SPECIFICATION REQUIREMENTS
Both the specifications controlled by DLA and those controlled internally by REA contain the following information.

a. Scope
b. Applicable Documents
c. Requirements
e. Packaging
f. Special Requirements

REA works with DLA to format information to comply with DLA SMD standard formatting requirements.

QUALITY SUPPORT DOCUMENTS
87XXXX R Specifications (refer to CSSP records in Intrepid for custom requirements)
SECTION 2.2.2  CONTROLLED DESIGN PROCEDURES AND TOOLS

GENERAL
The REA Chip Design methodology draws on proven and integrated tools that permit a designer to migrate a design concept from an objective specification or functional description to functional circuits. The REA Cadence Design System provides a basis for the design tools. The tools support simulation, performance analysis, physical layout, layout verification, and testability.

CONTROLLED DESIGN PROCEDURES AND TOOLS
The New Product Development Process (NPDP) program is designed to optimize the PTM (Product to Market) cycle times and improve the success rate of new product developments. The formalized NPDP procedure series provides guidelines and a methodology for product development, product planning, product definition, and market introduction. The NPDP procedure includes formal reviews at strategic points within the development cycle to ensure consistency in all areas of circuit development. Appropriate documentation is retained as Quality records. The REA Design System is a world class design system which contains tool sets for Analog, Mixed Signal, Power, RF Communication, and Digital designs. The Design System uses the defined core set of tools for front-end design, layout, and physical design verification. In addition to the core design tools, the design systems are tightly integrated with high performance tools and populated with advanced REA processes/libraries.

QUALITY SUPPORT DOCUMENTS

87XXXX  R Specifications (refer to CSSP records in Intrepid for custom requirements)
NPDP-XXXX  New Product Development Procedures
SECTION 2.2.3 PHOTOMASK SUBCONTRACTED

GENERAL
Photomasks are used in the Wafer Fab forming operations to transfer the patterns of the various levels of the IC design onto a photoresist coated wafer. All photomasks will be purchased through an approved subcontractor.

QUALITY SUPPORT DOCUMENTS
All Mask Fabrication procedures are documented in specification controlled by the supplier. All mask are ordered in conformance with requirements specified in purchase specification 210825-XXXX.
SECTION 2.2.4  WAFER FABRICATION AND ASSEMBLY CAPABILITIES

BASELINE

GENERAL
Records and information related to wafer fabrication and assembly capabilities covered by the QML program are in the Intrepid System.

SYSTEM
Each device type assigned to the QML program will be so designated in Intrepid. Attached to each of these device types are the die and package technology used. Wafer process and package capabilities are listed below.

WAFFER FAB CAPABILITIES
Reference section 3.3 for a list of QML Process Technologies.

ASSEMBLY CAPABILITIES

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<th>PACKAGE TYPES</th>
<th>LEAD FINISHES</th>
<th>DIE ATTACH MATERIAL</th>
</tr>
</thead>
<tbody>
<tr>
<td>CERDIP</td>
<td>SOLDER (SnPb)</td>
<td>SILVER GLASS</td>
</tr>
<tr>
<td>SIDE BRAZE DIP</td>
<td>(63/37% TIN/LEAD)</td>
<td>67-73% Ag</td>
</tr>
<tr>
<td>METAL CANS</td>
<td>GOLD (&gt;99.7%)</td>
<td>EUTECTIC GOLD (&gt;99.7%)</td>
</tr>
<tr>
<td>FLATPACKS</td>
<td></td>
<td>SILVER POLYMER</td>
</tr>
<tr>
<td>LCC</td>
<td></td>
<td>(79.5-80.5 Ag)</td>
</tr>
<tr>
<td>PGA</td>
<td></td>
<td>SILVER EPOXY</td>
</tr>
<tr>
<td>TO-257</td>
<td></td>
<td>(79% Ag)</td>
</tr>
<tr>
<td>SMD .5</td>
<td></td>
<td>SOLDIER</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(95% Pb/5% Sn)</td>
</tr>
</tbody>
</table>
SECTION 2.2.5 WAFER FABRICATION, ASSEMBLY & TEST FLOWS

GENERAL
Each product fabricated at REA is produced in accordance with a series of "traveler/flow" specifications. The traveler/flow describes the sequence of processes and references the appropriate unit process specification which describes how each process is to be executed. "Traveler/flows" are written for material fabrication, wafer fabrication, assembly, test, and post test processing. Wafer process and wafer level testing are defined in Section 2.2.9 Screening.

MASK, WAFER FABRICATION, ASSEMBLY & TEST FLOWS
All operations on the process flows used to fabricate, assemble, test, and monitor product will have appropriate work instructions. These work instructions will include, where appropriate, samples, drawings, and detailed operational instructions to ensure quality levels are maintained.

Through specified procedures, all designated support personnel, team members, and management are responsible for, and have the authority to, update work instructions to insure process and test procedures conform to expected practices and optimum quality systems. All applicable personnel are jointly responsible for ensuring the current work instructions are available.

Software control is the responsibility of the department who manages, administers, and/or uses the software. Procedures used to govern critical software are documented in internal process specifications.

QUALITY SUPPORT DOCUMENTS
All QML Product with corresponding flows/travelers are controlled by the electronic database “Intrepid”.
Generic flows for Design, Wafer Fabrication, Assembly, and Test are as follows:
PRODUCT FLOW

Subcontractors

- UMC is an approved subcontractor for Mask Generation and Wafer Fab Operations.
- Global (IBM) is an approved subcontractor for Mask Generation and Wafer Fab Operations.
- TowerJazz is an approved subcontractor for Mask Generation and Wafer Fab Operations.
- Amkor Philippines is approved for subcontractor services for Class Q assembly.
- KESM is approved for Burn-in subcontracted services for Class Q product.
- Millennium Microchip Technology (MMT) is approved for subcontractor services for Class Q assembly.
- Carsem Malaysia is approved for subcontractor services for Class Q test operation.
- Bridgepoint (Criteria Labs), Texas wafer level 100% testing (probe) Class Q and V.
BASIC DESIGN FLOW

APPROVED BUSINESS
& IMPLEMENTATION PLAN

DESIGN DEVELOPMENT PHASE
- PRODUCT ELECTRICAL/
  PHYSICAL DESIGN
- FORMAL REVIEW AND
  APPROVAL
  - DESIGN
  RELEASE

MANUFACTURING
DEVELOPMENT/DOCUMENTATION

MATERIAL PRODUCTION
VERIFICATION
- PRODUCT PERFORMANCE
- MANUFACTURABILITY
- RELIABILITY

PRODUCT RELEASE

MAINTENANCE PHASE
These Drawings and Specifications are the Property of Renesas Electronics Corporation and shall not be used, reproduced or copied without Written Permission.
Technologies/Products are defined by a specific flow (traveler). A unit process contained in the flow is evaluated by specific measurements such as:

* Diffusion/Implant
  - Junction Depth
  - Sheet Resistivity
  - Oxide Thickness
  - Implant Dose Calibration

* Deposited Films
  - Film Thickness
  - Refractive Index
  - Film Composition
  - Resistivity

* Photo Resist
  - Critical Dimension
  - Resist Thickness
  - Etch Rates

* Grind/Polish
  - Thickness

**NOTE:** Changes to process evaluations are approved per 999004.
Optional and if required are controlled via specific flows/travelers defined by the current best practice

1. RECEIVE DIE/WAFERS AND PAPERWORK

2. DIE/WAFTER STORES

3. ATTACH WAFER SAW/DIE INSPECT TRAVELER

4. DIE SEPARATION (Saw)
   - 100% SAW through ON TAPE- SILICON, SOS

5. DIE PEEL
   - MANUAL/AUTO, DIE PICK
   - RAD HARD SAMPLES Picked as required
   - (TOTAL DOSE RADIATION TESTING LEVEL IS AS SPECIFIED IN THE SMD DRAWING)
   - SEM SAMPLES AS REQUIRED

6. DIE SORT/CLEAN
   - CLASS V CONDITION "A"
   - CLASS Q CONDITION 'B'
   - CLASS Q CONDITION 'B' ALTERNATE
   - SOS STANDARD PRODUCT MODIFIED Cond. A
   - SOS STANDARD PRODUCT MODIFIED B Cond. B
   - CLASS T MODIFIED CONDITION B
   - DETAILS OF CLASS T VISUAL INSPECTION ARE IN 203790 AND ARE AVAILABLE IN INTREPID

7. DIE INSPECTION (HIGH POWER)

8. QUALITY DIE INSPECT/ Monitors
WAFER SAW AND DIE SORT CLASS Q, V, AND T
continued

Optional and if required are controlled via specific flows/travelers defined by the current best practice

QUALITY DIE INSPECT/MONITOR

DIE SALES

ASSEMBLE SAMPLE FOR APPLICABLE GROUP E QUALIFICATION TESTING AND TEST

FIRST LEVEL PACK

PRODUCT DISTRIBUTION CENTER PACK & SHIP

INTERNAL ASSEMBLY

TRANSFER TO ASSEMBLY FOR APPLICABLE GROUP V/Q/N/T PROCESSING

QML QUALITY MANAGEMENT PLAN

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Options and if applicable are controlled via specific flows/travelers defined by the current best practice.

* Mil-STD-750 Test methods are used for all RAD Hard Power IC Product processed from die attach through seal operations & centrifuge. The process is a Mil-PRF.19500 DSCC certified process for Power Products.
ASSEMBLY FLOW HERMETIC
Class Q and V
CONTINUED

NON-DESTRUCT BOND PULL
(IF REQUIRED)
  o 100% WIRES PULLED - CLASS "V" OR WHEN SPECIFIED
  o NOT APPLICABLE FOR CLASS "V" RAD HARD POWER IC

HYDROGEN FIRE
(SOLDER SEAL ONLY)

CLEAN/N2 BLOW-OFF
(OPTIONAL)

PRESEAL INSPECTION
(HIGH AND LOW POWER)
  o CLASS "V"/COND "A"
  o CLASS "Q"/COND "B"
  o CLASS "Q" ALTERNATE
  o SOS STD. PRODUCT MODIFIED "A"
  o SOS STD. PRODUCT MODIFIED "B"
  o CLASS "V" RAD HARD POWER IC
    Mil-STD-750

QUALITY PRESEAL MONITOR
(HIGH AND LOW POWER)
  o PER APPLICABLE VISUAL INSPECTION CLASS

CONTINUED -
ASSEMBLY FLOW HERMETIC CLASS Q AND V (CONTINUED)

SEAL
- FURNACE GLASS SEAL - CERDIPS
- FURNACE SOLDER SEAL - GOLD/TIN COMBO LIDS
- RESISTANCE WELD - NICKEL LIDS METAL CANS
- SEAM WELD - NICKEL/GOLD LIDS

TEMPERATURE CYCLE

CENTRIFUGE

PIND TEST (IF REQUIRED)
- ALL CLASS "V" OR CUSTOMER REQUIREMENTS

Sequence of events below may vary

FINE LEAK TEST

GROSS LEAK

FRAME REMOVAL (IF REQUIRED)
- MANUAL TRIMMING

TUBE AND CARRIER LOAD
- VISUAL INSPECTION -SAMPLE

QUALITY MONITOR (OPTIONAL)
- EXTERNAL VISUAL SAMPLE AND DATA REVIEW

SHIP TO TEST CONTINUED
(RETURNED TO ASSEMBLY FROM TEST)

LEAD FINISH
(IF REQUIRED)
- SOLDER * CERDIPS, SIDEBRAZE DIPS, METAL CANS, LCC
- GOLD- SIDEBRAZE DIPS, FLATPACKS, LCC, PGA, METAL CANS
- MAY BE PERFORMED AFTER BURN-IN AND ELECTRICAL TEST

QUALITY MONITOR
(OPTIONAL)
- EXTERNAL VISUAL AND DATA REVIEW

RESHIP TO TEST
Optional and if applicable are controlled via specific flows/travelers defined by current best practice. Monitors are to the same criteria as manufacturing operations.

Class T RAD Hard Power IC products will follow the Class S/Q Flow for the die attach through package seal operations.

**ATTACH ASSEMBLY TRAVELER**

**DIE ATTACH**
- GOLD EUTECTIC
- SILVER POLYMER
- SILVER GLASS

**QUALITY DIE ATTACH MONITOR**
- DIE SHEAR
- DIE PULL

**CLEAN/N2 BLOW-OFF**
*(OPTIONAL)*

**WIRE BOND**
- BOND PULL MONITOR
  - DESTRUCTIVE BOND PULL

**CONTINUED**
ASSEMBLY FLOW HERMETIC CLASS T
(CONTINUED)

CLEAN/N2 BLOW-OFF
(OPTIONAL)

PRESEAL INSPECTION
(HIGH AND LOW POWER)
  - CLASS T VISUAL PER 233750 (MODIFIED CONDITION B OF TEST METHOD 2010)
  - NOTE: INSPECTION DETAILS WILL BE MADE AVAILABLE UPON REQUEST

QUALITY PRESEAL MONITOR
(HIGH AND LOW POWER)

SOLDER SEAL
  - FURNACE SOLDER SEAL  GOLD/TIN COMBO LID
ASSEMBLY HERMETIC FLOW
CLASS T
(CONTINUED)

NOTE: Sequence of events below may vary

FINE LEAK SAMPLE TEST

FRAME REMOVAL
(IF REQUIRED)

- MANUAL TRIMMING

TUBE/CARRIER LOAD

QUALITY MONITOR
(OPTIONAL)

SHIP TO TEST
TEST OPERATIONS FLOW
CLASS Q and V

- OPTIONS. "If Applicable" are controlled via specific flows/travelers defined by special customer requirements or current best commercial practices.

LOT FORM

100% ELECTRIC TEST (OPTIONAL)
see Notes 1 and 2

BURN-IN (IF APPLICABLE)
- BURN-IN CONDITIONS eg STATIC OR DYNAMIC, ARE DEFINED IN THE APPLICABLE DETAIL DRAWING, AND INCLUDED IN THE PART SPECIFIC FLOW
  - See Note 3
- POST BURN-IN ELECTRICAL (See Notes 1 and 2)
- APPLY APPLICABLE PDA
- OPTIONAL ELECTRICAL TEST MONITOR/ ALTERNATE GROUP "A" AS DEFINED BY PRODUCT SPECIFIC TRAVELER

SOLDER DIP (IF APPLICABLE)
- VISUAL
- SOLDERABILITY MONITOR
TEST OPERATIONS FLOW
CLASS Q and V
CONTINUED

BRAND

- FLOW DEPENDENT - BRAND MAY
- BE COMPLETED PRIOR TO BURN-IN.

FINAL ELECTRICAL TEST
PER APPLICABLE DEVICE
SPECIFICATION

- SEE NOTE 1 AND 2
- ELECTRIC TEST MONITOR
- (ALTERNATE GROUP "A" if applicable)

QUALITY (TCI) TESTING
(AS APPLICABLE)

- HERMETIC - APPLICABLE GROUPS B, C, D, AND E TESTING
- REFERENCE Section 2.10 / 2.2.10

VISUAL/MECHANICAL

FINAL ACCEPTANCE

PACK AND SHIP

Title: QML QUALITY MANAGEMENT PLAN
Specification Type: DOCS
Specification Number: 999015
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NOTES

NOTE 1: 100% of the product will receive a minimum of one electrical test insertion per the manufacturing flow.

NOTE 2 Typical test temperatures are:

<table>
<thead>
<tr>
<th>MINIMUM</th>
<th>MAXIMUM</th>
<th>GRADE</th>
</tr>
</thead>
<tbody>
<tr>
<td>- 0°C</td>
<td>+ 70°C</td>
<td>Commercial</td>
</tr>
<tr>
<td>- 40°C</td>
<td>+ 85°C</td>
<td>Industrial</td>
</tr>
<tr>
<td>- 55°C</td>
<td>+ 125°C</td>
<td>Military</td>
</tr>
</tbody>
</table>

NOTE 3 Typical burn-in, when specified, is 160 hours at 125°C for Class Q and 240 hours at 125°C for Class V. Standard time/temperature regression tables in the product flow shall be used when applicable.
TEST OPERATION FLOW
CLASS T

- OPTIONS. "If Applicable" are controlled via specific flows/travelers defined by current best practices.

LOT FORM

100% ELECTRIC TEST (Optional Flow Dependent)

BURN-IN

- BURN-IN CONDITIONS e.g. STATIC OR DYNAMIC, ARE DEFINED IN THE INTERSIL PART SPECIFIC APPLICABLE DETAIL DRAWING, 160 HOURS AT 125°C OR 120 HOURS AT 135

- PART SPECIFIC FLOW OPTIONAL POST BURN-IN ELECTRICAL (Room/low/high)

BRAND

VISUAL MECHANICAL (SAMPLE)

FINAL ACCEPTANCE

QUALITY TESTING (AS APPLICABLE)

- APPLICABLE GROUPS B,C,D AND E TESTING REFERENCE SECTION 2.2.10

PACK AND SHIP

- MAY INCLUDE SILVER EPOXY DIE ATTACH INVENTORY
SECTION 2.2.6  QML LISTING COVERAGE

GENERAL
An electronic database is maintained which lists all QML part types and their corresponding die technologies and package/assembly technologies.

QML LISTING COVERAGE SYSTEM
A listing of all QML part types and their corresponding die technologies and package/assembly technologies is maintained in the "Oracle (COBRA)" and "Intrepid" database systems.

QUALITY SUPPORT DOCUMENTS

999017  Product Number and Structure Definitions
SECTION 2.2.7  PM/TCV/SEC PROGRAM

GENERAL
At REA a Process Monitor (PM) and a Technology Characterization Vehicle (TCV) are designed for each die technology.

A PM is used to obtain key electrical and physical data on product as it is being fabricated for the purpose of process control, scrap/continue processing decisions and a database for design model verification.

The TCV is used to characterize a technology's susceptibility to wear-out reliability failure mechanisms such as Electromigration, TDDB, etc.

Standard Evaluation Circuits (SEC)s may be an actual device selected for TCI (Technology Conformance Testing) testing or a special design qualification circuit. The SEC may be used as a surrogate for the purposes of TCI testing and as a vehicle for various yield improvement projects or RAD hard evaluations.

REA typically conforms to the microcircuit grouping for test coverage and does not utilize the allowed SEC program.
Reference paragraph 3.3 for a list of PM’s and TCV’s by technology

PROCESS MONITORS PROGRAM
Process Monitors are designed for measuring the wafer level electrical parameters and are on every wafer manufactured. The PM's are part of the Wafer Acceptance Testing consistent with standards for high quality and reliability. This electrical data is used for feedback to the Wafer Fab, provides pass/fail data relative to the wafers continuing processing, and provides a database for design to verify device models. Structures are also available for assessment of radiation effects, monitoring of oxide charge trapping, and other tests.
TECHNOLOGY CHARACTERIZATION VEHICLE PROGRAM
The TCV contains the structures necessary to fully characterize each process technology for each of the following "wear-out" mechanisms:

A. Electromigration
B. Hot carrier aging
C. Time dependent dielectric break down
D. Ohmic contact degradation

The designs of the TCV structures are to worst case design ground rules. Each TCV is fully processed through glassivation. The structures can exist in a fully independent mask set or as part of the PM or SEC. During the initial Reliability qualification of each new technology, the TCV structures are stressed to failure and statistically characterized. Once in production, the "wear-out" mechanisms are monitored on each run via the use of a critical node list. In addition design ground rules are modified, if necessary, to provide guard bands for guaranteeing sufficient life times.

STANDARD EVALUATION CIRCUIT PROGRAM
The SEC for each technology is either a product or a specially designed circuit. The SEC is used as a surrogate to demonstrate process reliability for the technology via TCI (Technology Conformance Inspection) testing. SEC's are selected from standard products or are specially designed on the basis of worst case design rules and level of complexity. For RHA environment, the SEC utilizes all relevant radiation hardness assurance design rules.

QUALITY SUPPORT DOCUMENTS
230415-QML Reliability Qualification Specification – QML
SECTION 2.2.8 INCOMING INSPECTION & VENDOR CONTROL PROCEDURES

GENERAL
Engineering, Purchasing, Manufacturing and Quality Assurance have established a system to insure that purchased materials conform to specified requirements.

INCOMING INSPECTION & VENDOR CONTROL SYSTEM
Reference the sections regarding "Control of externally provided processes, products and services" section 8.4 of the REA Quality Manual.
SECTION 2.2.9 SCREENING

GENERAL
All QML integrated circuits shall be subjected to and pass the screening tests as specified in the Screening Tables that follow. (Reference Class Q, Figure 2.2.9 A Class T Figure 2.2.9B, Figure 2.2.9C Class V)

A screening test may be eliminated or modified by the TRB when reliability data justifies the change. The qualifying activity will be notified of such changes. Approval from the qualifying activity is required for Class V product. (Reference Appendix B Para B.3.1 of MIL-PRF-38535)

MICROCIRCUIT SCREENING
Screening is performed in accordance with the wafer fab, assembly and test travelers. These travelers reference process specifications required to perform the appropriate screening tests.

QUALITY SUPPORT DOCUMENTS
233XXX Quality Procedures
240111-XXX QCI Test Inspection Procedures - Palm Bay
### Screening Tables

#### Class Q  
**Figure 2.2.9A**

<table>
<thead>
<tr>
<th>Screen</th>
<th>MIL-STD-883 test method</th>
</tr>
</thead>
<tbody>
<tr>
<td>1. Wafer acceptance</td>
<td>Sample PM electrical</td>
</tr>
<tr>
<td>2. Internal visual</td>
<td>2010 SOS/SCD Compliant Grandfathered material</td>
</tr>
<tr>
<td>3. Temperature cycling</td>
<td>1010</td>
</tr>
<tr>
<td>4. Constant acceleration</td>
<td>2001</td>
</tr>
<tr>
<td>5. Serialization</td>
<td>In accordance with device procurement specification</td>
</tr>
<tr>
<td>6. RAD Inspection</td>
<td>1019 RAD Level as specified in SMD</td>
</tr>
<tr>
<td>7. Interim (pre burn-in) electrical parameters</td>
<td>In accordance with device procurement specification</td>
</tr>
<tr>
<td>8. Burn-in test</td>
<td>1015</td>
</tr>
<tr>
<td>9. Interim (post burn-in) electrical parameters</td>
<td>In accordance with device procurement specification</td>
</tr>
<tr>
<td>10. Percent Defective Allowable (PDA) calculation</td>
<td>All lots or as required by device procurement specification</td>
</tr>
<tr>
<td>11. Seal test</td>
<td>1014</td>
</tr>
<tr>
<td>a. Fine</td>
<td></td>
</tr>
<tr>
<td>b. Gross</td>
<td></td>
</tr>
<tr>
<td>12. External visual</td>
<td>2009</td>
</tr>
</tbody>
</table>

#### Class T  
**Figure 2.2.9B**

<table>
<thead>
<tr>
<th>Screen</th>
<th>MIL-STD-883 test method or TRB/DLA approved alternate test method</th>
</tr>
</thead>
<tbody>
<tr>
<td>1. Wafer Lot Acceptance</td>
<td>PM electrical, SEM inspections, thickness and CV measurements are per the standard Class Q monitor program.</td>
</tr>
<tr>
<td>2. Internal Visual</td>
<td>2010 Condition B modified per 233750 (REA internal specification available upon request)</td>
</tr>
<tr>
<td>3. RAD Inspection</td>
<td>1019 RAD level as specified in the SMD</td>
</tr>
<tr>
<td>4. Interim Pre Burn-in Electrical Parameters</td>
<td>In accordance with device procurement specification</td>
</tr>
<tr>
<td>5. Burn-in</td>
<td>1015</td>
</tr>
<tr>
<td>6. Final Electrical Test</td>
<td>In accordance with device procurement specification</td>
</tr>
<tr>
<td>7 Seal test (Sample)</td>
<td>1014 For devices assembled in solder seal packages the fine and gross leak seal test will be performed after the seal operation. The test will not be performed after the lead shearing/clipping or between the final electrical testing and external visual inspection operation. Time restrictions between die mount and seal do not apply</td>
</tr>
<tr>
<td>8. External Visual</td>
<td>2009</td>
</tr>
</tbody>
</table>
## QML QUALITY MANAGEMENT PLAN

<table>
<thead>
<tr>
<th>Screen</th>
<th>MIL-STD-883 test method or TRB/DLA approved alternate test method</th>
</tr>
</thead>
</table>
| 1. Wafer Lot Acceptance | 5007 Plus PM Electrical samples  
*DLA approved acceptance criteria.  
Note 1 & 2. For SEM step coverage  
Note 3 & 4 for CV Test optimization.  
Note 5 SEM re-inspection of previously SEM qualified material.  
Note 6 for SEM Inspection Certification Requirements  
Note 7 SEM Sampling for product in die form  
Note 8 Alternate SEM for UHF2CMOS, P6 and UHF2 BI-CMOS Technologies |
| 2. Nondestructive Bond Pull | 2023 or Approved Alternate  
(Not applicable for RAD Hard power IC) |
| 3. Internal Visual | 2010 SOS/SCD Compliant Grandfathered material Reference Section 3.3 for Special AV/SI criteria |
| 4. Temp Cycle | 1010 |
| 5. Constant Acceleration | 2001 |
| 6. PIND | 2020 |
| 7. Serialization | In accordance with device procurement specifications  
(DLA approved lot formation allows 6 weeks Seal Window) |
| 8. Radiographic Inspection | 2012 |
| 9. Interim Pre Burn-in Electrical Parameters | In accordance with device procurement specification |
| 10. Burn-in | 1015 |
| 11. Interim (Post Burn-in) Electrical Parameters | In accordance with device procurement specification |
| 12. Reverse Bias Burn-in | 1015 |
| 13. Interim (Post Burn-in) Electrical Parameters | In accordance with device procurement specification |
| 14. PDA Calculation | All lots or as required by device procurement specification |
| 15. Final Electrical Test | In accordance with device procurement specification |
| 16. Seal test | 1014 For devices assembled in solder seal packages at the Palm Bay Facility the fine and gross leak seal test will be performed after the centrifuge operation. The test will not be performed after the lead shearing/clipping or between the final electrical testing and external visual inspection operation. |
| 17. External Visual | 2009 |
| 18. RAD Inspection | 1019 RAD level as specified in the SMD |

As of Seal Date code “0815”, all Class “V”, “S” and Condition “A” product sealed on or after 6th April 2008 in Palm Bay, will receive a 100% Gross Leak Test.
NOTE 1: Product that does not meet step coverage requirements per MIL-STD-883, Method 2018 will be evaluated for minimum metal thickness requirements using the following criteria:
1) Current density of 2E5 A/CM2
2) Electro migration rules for the applicable technology
3) A minimum thickness of 2000 angstroms for mechanical integrity
The thickest metal requirement calculated to meet the appropriate metal thickness will be used as the acceptance criteria for step coverage.

NOTE 2: Reference Section 3.3 for Special AVSLI acceptance criteria for moly.

NOTE 3: CV metal wafer lot for Test Method 5007 may be:
For CV acceptance using high vacuum, load lock metallization systems, all product processed through metal deposition under a continuous vacuum will be considered a wafer lot for CV testing and wafer lot acceptance

NOTE 4: CV monitor for gate oxide for Test Method 5007 may be:
The gate oxide for Class S devices will be monitored to the most stringent condition defined in test Method 5007 at the frequency specified in the internal process specification.

NOTE 5: The following sample plan will be used to reinspect and document step coverage results for product inventory previously SEM qualified to the full sample and test requirements in affect at the time of the original SEM.

Product in Wafer Form
Two random wafers will be selected and inspected per the requirements in the QM Plan 999015.

Product in Die Form
- A total of 8 die from each wafer lot will be randomly selected and inspected per the requirements in the QM Plan 999015.

NOTE 6: Class V SEM Inspection Certification will be performed initially and for reinstatement after decertification as specified in specification 236000, when reports are reviewed, approved and signed off by engineering.

NOTE 7: SEM Sampling for product in die form
On rare occasions the die are scribed, sorted and loaded into die trays without selecting the sample for the specific wafer quadrants.
On these occasions the following alternate SEM sample selection procedure will be used.
- A Material Review Board that includes the CORE TRB members for Wafer Fab will review the product history, process technology characteristics, etc. and approve the use of the alternate sample plan on a case by case basis.
- The practice of transferring uninked die from the wafer into die trays is to start at the top of the wafer and place electrical good units in sequential order working from left to right across the wafer and loading the tray left to right until the die transfer is complete.
- Wafer identity is maintained by die tray.
- Operators will randomly select two wafers from the lot for SEM inspection.
- The individual die will be selected as follows:
  - Divide the number of die trays for each selected wafer by four.
  - Use the resulting whole number to select the trays to be sampled.
Example: Wafer #5 was selected for inspection and has a total of 12 die trays (12÷4=3) Sample from trays 3, 6, 9 and 12

NOTE 8: Alternate SEM acceptance method for UHF2 CMOS, P6, P6SOI AND UHF2 BI-CMOS Technologies
The planar process eliminates oxide steps that generate metal step coverage issues that are traditionally screened using Test Method 2018 inspection criteria. Five positions on each wafer in the lot are electrically tested to verify metal integrity including step coverage. The failure of one test site for metal integrity from the five sites tested will reject the wafer.
SECTION 2.2.10  TECHNOLOGY CONFORMANCE INSPECTION (TCI) PROCEDURES

GENERAL
TCI testing is performed on a periodic basis to assure that the quality and reliability requirements of QML product are being met. TCI testing includes applicable groups A, B, C, D & E-inspections for Class V, Class Q, and Class T product.

TECHNOLOGY CONFORMANCE INSPECTION (TCI) PROCEDURES
Notes from DLA approved test optimization implementation are applicable for all Class V, Q, and T product unless stated for a specific class or manufacturing location.

<p>| Class Q | Sample sizes, MIL-STD-883 test methods, test method sequence, etc. for group A, B, C, D &amp; E testing are documented and are in compliance with MIL-PRF-38535 unless test optimization has been implemented as defined in the notes following the Class V table. Inspection lot definitions are also documented in internal specifications |</p>
<table>
<thead>
<tr>
<th>QCI Requirements</th>
<th>QCI Vehicle</th>
</tr>
</thead>
<tbody>
<tr>
<td>Group A testing 4/</td>
<td>Actual Device</td>
</tr>
<tr>
<td>Group B testing 3/</td>
<td>Actual Device</td>
</tr>
<tr>
<td>Group C testing 2/</td>
<td>SEC or Actual Device</td>
</tr>
<tr>
<td>Group D testing 1/</td>
<td>SEC or Actual Device</td>
</tr>
<tr>
<td>Group E testing *</td>
<td>Actual Device</td>
</tr>
<tr>
<td>* = Group E performed as required to the level in the SMD drawing</td>
<td></td>
</tr>
</tbody>
</table>

<p>| Class T |
|-------------------|-------------|</p>
<table>
<thead>
<tr>
<th>QCI Requirements</th>
<th>QCI Vehicle</th>
</tr>
</thead>
<tbody>
<tr>
<td>Group B testing 3/</td>
<td>Actual Device</td>
</tr>
<tr>
<td>Group C testing 2/</td>
<td>SEC or Actual Device</td>
</tr>
<tr>
<td>Group D testing 1/</td>
<td>SEC or Actual Device</td>
</tr>
<tr>
<td>Group E testing (Reference SMD for RAD level testing requirements)</td>
<td>Actual Device</td>
</tr>
</tbody>
</table>

- Class V and Class Q test results may be used as an approved reference when available. As a minimum Class T endpoint subgroup testing will be the same as Class Q
- Sample frequency
  - Group B Monthly by seal date, die attach, and package group
  - Group C once every 4 Fab. Quarters by microcircuit group
  - Group D Every 26 weeks of production by assembly site, seal date and die attach

Title: QML QUALITY MANAGEMENT PLAN  
Specification Type: DOCS  
Specification Number: 999015  
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Class V

Sample sizes, MIL-STD-883 test methods, test method sequence, etc. for group A, B, C, D & E testing are documented and are in compliance with MIL-PRF-38535 unless test optimization has been implemented as defined in the notes following this table. Inspection lot definitions are also documented in internal specifications.

<table>
<thead>
<tr>
<th>QCI Requirements</th>
<th>QCI Vehicle</th>
</tr>
</thead>
<tbody>
<tr>
<td>Group A testing 4/</td>
<td>Actual Device</td>
</tr>
<tr>
<td>Group B testing 3/</td>
<td>Actual Device</td>
</tr>
<tr>
<td>Group C testing 2/</td>
<td>Actual Device or SEC</td>
</tr>
<tr>
<td>Group D testing 1/</td>
<td>SEC or Actual Device</td>
</tr>
<tr>
<td>Group E testing *</td>
<td>Actual Device</td>
</tr>
</tbody>
</table>

* = Group E performed as required to the Level in the SMD drawing

Note 1: Group D QML - DLA approved Best Practice
Inspection windows will be maintained by die attach and assembly site.
REA will maintain a total of six package families consisting of twelve package groups
Package families and window groups are as follows:
  CERDIP 3-groups
  Multilayer - Metal Lid Packages 1-group
  Multilayer - Ceramic Lid Packages 1-group
  Can 2-groups
  CERPACK/CERQUAD 3-groups
  Power Packages 2-groups
End point electricals will be at room temperature electrical test only
Lead finish will not be a QCI window grouping factor
Critical members of the TRB will review the root cause of any Group D failures
Product containment and additional testing will be determined based on data analysis and product reliability considerations.

Note 2: Group C Approved Test Optimization
Die attach material will not be a factor in maintaining Group C windows.
Class V Life Test results may be used as an approved reference for a lesser Hermetic QML grade when from the same diffusion lot.

Note 3: Group B Approved Test Optimization
Bond strength testing is not required as part of the Group B Test subgroups

Note 4: Group A Approved Test Optimization
Group A testing for room, high, low temperature testing is device specific for product tested at the Palm Bay Facility. Actual product is controlled by the Intrepid system. Product additions must be approved by the TRB

QUALITY SUPPORT DOCUMENTS

240111-XXX QML, QCI Inspection Procedures (Domestic)
SECTION 2.2.11  MARKING

GENERAL
Marking of QML microcircuits shall be in accordance with the detail specification or drawing (excluding die) and shall be legible, complete and meet the resistance to solvents requirements of MIL-STD-883, Method 2015.

MARKING
The marking of each QML microcircuit shall be as specified by the traveler and shall include:

a. The index point
b. PIN (Part Identification Number)
c. "Q" or "QML" certification mark
d. Manufacturers identification (as space permits)
e. Country of origin
f. Date code
g. Special marking
h. Electrostatic Discharge Sensitivity identifier

All the brand elements as stated will be specified by the traveler, or electronic media. Container marking shall include all of the marking requirements as stated above with the exception of the index point, serialization, and “Q” or “QML” certification mark.

SUBCONTRACTOR AND PALM BAY ASSEMBLY MARKING
Subcontractor assembly supplier codes are marked as follows:
ChipPAC Malaysia = Code H
Millennium Microtech = Code R
Amkor Philippines = Code L
REA Palm Bay = Code X

QUALITY SUPPORT DOCUMENTS
999053    Intrepid Application
999017    Product Number and Structure Definition
597002    Brand Specification Palm Bay
Applicable part specific Brand Pack Card (BPC) documents as defined in Intrepid
SECTION 2.2.12 REWORK

GENERAL
Rework or reprocessing devices or part thereof through a manufacturing operation shall be documented in accordance with the internal procedures and performed subsequent to the next manufacturing operation.

REWORK
Rework documentation for wafer fab, assembly and test are clearly specified in internal procedures. Operations that allow reworks are in compliance with MIL-PRF-38535. Documented processes procedures are included in the REA Specification System.
SECTION 2.3 FUNCTIONAL ORGANIZATION CHART

GENERAL

The organizational chart for Renesas Electronics America Inc. is not publicly available, general functional reporting covering the TRB, Quality Assurance and production is shown below:
SECTION 2.4 CHANGE CONTROL PROGRAM

GENERAL
All changes to the QML program that could potentially have an effect on the quality, reliability, performance, or interchangeability of the resulting microcircuits shall be evaluated and approved by the members of the technical review board.

CHANGE CLASSIFICATION
All changes critical to the QML program are defined in appendix A "Guidelines for Change Classification" of specification 999004 'Change Notification Policy and Procedure'.

CHANGE PROCEDURES
The change control procedure is described in specification 999004 'Change Notification Policy and Procedure'.

QUALITY SUPPORT DOCUMENTS

<table>
<thead>
<tr>
<th>Specification</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>999004</td>
<td>Change Notification Policy and Procedure</td>
</tr>
<tr>
<td>DOC-PROC-ALL</td>
<td>Specification Control Procedures (Document Control)</td>
</tr>
<tr>
<td>999056-MASK</td>
<td>Change Review procedures for design changes</td>
</tr>
<tr>
<td>999056-PAT</td>
<td>Change Review procedures for Probe, Assembly, Test/Post Test</td>
</tr>
<tr>
<td>999056-FAB</td>
<td>Change Review Procedures for Wafer Fab and Wafer Fab Related operations</td>
</tr>
</tbody>
</table>
QML CHANGE CONTROL PROGRAM FLOW

ECN INITIATED

*FUNCTIONAL TRB MEMBER REVIEWS FOR MAJOR/MINOR CHANGE

MAJOR CHANGE 999004

PROCESS PER STANDARD DOC. CONTROL PROCEDURE

FUNCTIONAL TRB MEMBER APPROVAL AND SUBMIT TO TRB

CHANGE DOCUMENTED? ADEQUATE SUPPORTING DATA? REQUIRED QUAL COMPLETE?

RETURN TO ORIGINATOR

FUNCTIONAL TRB MEMBER WITH SPECIFIC PROCESSING EXPERTISE AND 999004 KNOWLEDGE ON SUBJECT BEING CHANGED.
SECTION 2.5  FAILURE ANALYSIS PROGRAM

GENERAL
REA has established a failure analysis program, which analyzes failures from a wide variety of sources for determining the root cause of failure so that a meaningful corrective action and subsequent continuous improvement can be obtained. All failure analysis procedures have been established in accordance with MIL-STD-883, Method 5003.

FAILURE ANALYSIS PROGRAM
The responsibility of the Failure Analysis Laboratory is to provide the technical capabilities, equipment and personnel, necessary to support in-depth failure analysis of REA products. The analysis encompasses the isolation and identification of all failure modes/failure mechanisms, writing a comprehensive technical report and the assignment of appropriate corrective actions. Development of the capabilities for failure analysis also extends into research vital to understanding the basic physics of the failure.

Failure analysis is performed as a method of enhancing product quality and reliability and determining corrective actions. Failure analysis is the final and crucial step used to isolate potential reliability problems that may have occurred during reliability stressing. Accurate analysis results are imperative to assessing effective corrective actions. To ensure the integrity of the analysis, correlation of the failure mechanism to the initial electrical failure is essential throughout the failure analysis flow.

A general failure analysis procedure (see figure 2.5.A) has been established in accordance with the current revision of MIL-STD-883, Method 5003. The analysis procedure was designed on the premise that each step should provide information on the failure without destroying information to be obtained from subsequent steps. The exact steps used for an analysis are determined by laboratory personnel and contain data, the failure analyst's notes, the formal Product Analysis Report and the Failure Analysis Report.

The Failure Analysis Laboratory performs all analysis required internally and externally for customers as described in Figure 2.5.B.

QUALITY SUPPORT DOCUMENTS

230354  Procedure for Failure Analysis
Failure Analysis Flow (Non-Destructive)

- External Inspection
- Fail signature
- Final Leak Test
- Gross Leak Test
- Electrical Analysis

Failure Analysis Flow (Destructive)

- Process Data
- Research Data
- Circuit History
- Deencapsulation
- Internal Visual Inspection
- Internal Electrical Probe
- Analysis

Special Tests
- Failure Mode Predictions

Select Analysis Path

Physical Tests
- Chemical Tests
- Cross Section

Analysis Report

Figure 2.5.A
**Title:** QML QUALITY MANAGEMENT PLAN

**Specification Type:** DOCS  
**Specification Number:** 999015  
**Issue:** 42  
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**Image Description:**

The image shows a flowchart titled **Internal Reliability Program**. The chart is divided into several sections, including:

- **Internal Reliability Program**
- **(TCI) Qualification Testing**
- **Special Prod. Eng. Reliability Evaluations**
- **Reliability Engineering Evaluations**
- **Customer Returns**
- **Production Problems**
- **Development Problems**

The flowchart illustrates the process from **Failed Devices** to **Support Analysis** through various stages such as **RA**, **QA**, **Diagnostic Technique Development**, and **Corrective Action**. The flowchart includes a reference to **Figure 2.5.B**.
SECTION 2.6  SELF AUDIT PROGRAM

GENERAL
The internal quality audit is an essential element of the quality system. Regular audits are performed to ensure conformance to the overall quality system, specified process procedures, and specific customer requirements. Review of audit results identifies opportunities for continuous quality improvements.

SELF AUDIT PROGRAM
SECTION 2.7 TRB OPERATING PROCEDURES

GENERAL
REA has established a multi-disciplined TRB organization which is responsible for the development and maintenance of a Quality Management (QM) Plan, maintenance of all certified/qualified processes, process change control, reliability data analysis, failure analysis, corrective actions, QML microcircuit procedures, qualification status of the technology and reporting QML status to DLA.

TRB SYSTEM
The TRB is a multi-functional group representing worldwide operations. QML operations are located worldwide as shown in figure 3.2.A. The general TRB change control flow is shown in Figure 2.7.A.

The subcontractor quality team located in Malaysia is responsible for reviewing all change notifications from the subcontractor. The Palm Bay TRB will review and approve major changes per guidelines established in 999004.

The Design Centers at the Palm Bay and Research Triangle Park locations are the only design active facilities for QML products. Issues related to products initially designed at the New Jersey facility are communicated through the TRB product engineering representatives. Each member is responsible for keeping management current on TRB/QML activities.

The Palm Bay TRB reviews and approves all subcontractor major changes.

The QML Coordinator is an active member of the Palm Bay TRB and coordinates all change communication to DLA and the end customer as appropriate.

DLA REPORTING REQUIREMENTS
The QML coordinator will notify DLA on a real time basis of major changes to product and or business activities. The notification will contain sufficient detail to provide DLA a basis for acceptance of the change.

On an annual basis, the QML coordinator will submit to DLA a status report in a format consistent with MIL-PRF-38535 appendix G paragraph G.3.2.3 and specification 999009 (Palm Bay “Technical Level” TRB – Rules and Procedures).
QUALITY SUPPORT DOCUMENTS

999009 Palm Bay “Technical Level” TRB Rules and Regulations
999004 Change Notification Policy and Procedures
999056-MASK Change Review Procedures for design changes
999056-PAT Change Review Procedures for Probe, Assembly and Test
999056-FAB Change Review Procedures for Wafer Fab and Wafer Fab Related Operations
Subcontractor Request for Change Through PCRB
Majors Move to TRB

REINESAS TRB

REINESAS QML COORDINATOR (MEMBER OF TRB)

DLA

REINESAS MARKETING REP

Figure 2.7.A
SECTION 2.8 YIELD/QUALITY IMPROVEMENT PROGRAM

GENERAL
REA operates on a policy of continuous improvement through the use of extensive employee involvement. To this end REA utilizes employee involvement teams (EIT’s) and system involvement programs (SIP’s) in continuous improvement activities using a variety of “problem solving” techniques. These continuous improvement activities are initiated when a need is identified by an area Team, Engineer or member of management.

YIELD/QUALITY IMPROVEMENT PROGRAM
REA has established 5 principles which guide its quality improvement efforts. These principles are customer focus, continuous improvement, employee involvement, supplier partnerships and highest standards of conduct, ethics and integrity. Each of these principles contributes to overall quality improvement. Both exempt and non-exempt employees can be involved in EIT’s or SIP’s. The appropriate levels of membership will be determined when the Team activity is initiated. Members of the various teams are trained in “team techniques” and “problem solving” methods in accordance with the training program available at their facility.

At the heart of all continuous improvement efforts is a corrective action system. Reference “Improvement”, section 10 of REA’s Quality manual.
SECTION 2.9  SPC PROGRAM

GENERAL
Organized SPC activity at Renesas Electronics America Inc. began in 1982 and has since matured into a culture that embraces SPC as a “way of doing business”. Statistical Process Control is a significant tool used to achieve the goal, “to meet or exceed internal and external customer expectation”, by providing continuous improvements in quality, value, and delivery of products and services. SPC for all designated critical processes are compliant to EIA 557 requirements.

SPC SYSTEM OF CONTROL
SECTION 2.10 LIST OF TEST METHODS FOR LAB SUITABILITY

GENERAL

Reference SECTION 2.2.10 for the Tables of Technology Conformance Test requirements for Class Q, V, and T. Testing is completed per MIL-STD-883 Method 5004/5005 and/or as defined by approved test optimization conditions documented in Section 2.2.10.

In the event of test equipment capacity restraints, the TRB may approve the use of a DLA approved test lab. The QML Coordinator will notify DLA of the temporary use of an alternate site not listed herein.

The SEM monitor program for Class Q product defined in MIL-PRF-38535, A.3.4.1.2.1 and A 3.4.1.2 has been modified as follows

The sample frequency and family groupings were determined by using the following guidelines.

- Product Family Identification and Sampling
  - Group Technologies will be classified as families by process structure that impact step coverage and the wafer fabrication location.
- New QML technologies/products will be standalone products and sampled on a routine basis until process controls demonstrate that there are no step coverage issue and the TRB approves the sample elimination.
- Class V lot acceptance SEM inspection data may substitute as the process monitor for the family process monitor requirements.
- Sampling and family groupings were approved by the TRB with DLA notification. The groupings are specified in document 241104.
- Routine SEM monitoring is not required for the following technologies:
  - HBC-10
  - HPA-2
  - HVTDLM
  - SAJI5/6
### LIST OF TEST METHODS AND LOCATIONS FOR LAB SUITABILITY

**TABLE 2.10 A**

List of Lab Suitability by Location, Basic Test Method and Condition

<table>
<thead>
<tr>
<th>Test Name</th>
<th>Method / Conditions</th>
<th>REA</th>
<th>Carsem</th>
<th>MMT</th>
<th>Amkor</th>
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<tbody>
<tr>
<td>Moisture Resistance</td>
<td>1004</td>
<td>X</td>
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<tr>
<td>Steady State Life Test</td>
<td>1005/A-E</td>
<td>X</td>
<td>X</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Salt Atmosphere</td>
<td>1009/A-D</td>
<td>X</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Temperature Cycling</td>
<td>1010/A-F</td>
<td>X</td>
<td>X</td>
<td>X</td>
<td></td>
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<tr>
<td>Thermal Shock</td>
<td>1011/B,C</td>
<td>X</td>
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<td></td>
</tr>
<tr>
<td>Seal</td>
<td>1014/A1,A2,B,C</td>
<td>X</td>
<td>X</td>
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<tr>
<td>Burn-in</td>
<td>1015/A-E</td>
<td>X</td>
<td>X</td>
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<tr>
<td>Internal Water Vapor Cont.</td>
<td>1018</td>
<td>X²</td>
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<tr>
<td>Steady State Total Dose Irradiation</td>
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<td></td>
<td></td>
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<td></td>
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<tr>
<td>Constant Acceleration</td>
<td>2001/A-E</td>
<td>X</td>
<td></td>
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<td>X</td>
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<tr>
<td>Mechanical Shock</td>
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<td>Solderability</td>
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<td>Lead Integrity</td>
<td>2004/B1,B2,D</td>
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<td>X</td>
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<tr>
<td>Vibration, Variable Freq.</td>
<td>2007/A</td>
<td>X</td>
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<tr>
<td>External Visual</td>
<td>2009</td>
<td>X</td>
<td>X</td>
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<tr>
<td>Internal Visual</td>
<td>2010/A,B</td>
<td>X</td>
<td></td>
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<tr>
<td>Bond Strength</td>
<td>2011/C,D</td>
<td>X</td>
<td></td>
<td>X</td>
<td>X</td>
</tr>
<tr>
<td>Radiography</td>
<td>2012</td>
<td>X</td>
<td></td>
<td></td>
<td></td>
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<tr>
<td>Internal Visual for DPA</td>
<td>2013</td>
<td>X</td>
<td></td>
<td>X</td>
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<tr>
<td>Internal Visual and Mechanical</td>
<td>2014</td>
<td>X</td>
<td></td>
<td></td>
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<tr>
<td>Resistance to Solvents</td>
<td>2015</td>
<td>X</td>
<td>X</td>
<td>X</td>
<td>X</td>
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<tr>
<td>Physical Dimensions</td>
<td>2016</td>
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<td>SEM</td>
<td>2018</td>
<td>X³</td>
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<td>Die Shear Strength</td>
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<td>X</td>
<td>X</td>
<td>X</td>
<td>X</td>
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<tr>
<td>PIND</td>
<td>2020/A,B</td>
<td>X</td>
<td></td>
<td>X</td>
<td>X</td>
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<tr>
<td>Glassivation</td>
<td>2021</td>
<td>X</td>
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<tr>
<td>Test Name</td>
<td>Method / Conditions</td>
<td>REA</td>
<td>Carsem</td>
<td>MMT</td>
<td>Amkor</td>
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<tr>
<td>------------------------</td>
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<td>-----</td>
<td>--------</td>
<td>-----</td>
<td>-------</td>
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<tr>
<td>Layer Integrity</td>
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<tr>
<td>Nondestructive Bond Pull</td>
<td>2023</td>
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<tr>
<td>Lid Torque</td>
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<tr>
<td>Adhesion of Lead Finish</td>
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<td></td>
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<td></td>
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<tr>
<td>Substrate Attach Strength</td>
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<td></td>
<td></td>
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<td>ESDS</td>
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<td>Terminal Capacitance</td>
<td>3021</td>
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<td>Wafer Lot Acceptance</td>
<td>5007</td>
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<tr>
<td>Electrical Test</td>
<td>Device Spec.</td>
<td>X</td>
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<td>X</td>
</tr>
</tbody>
</table>

1. Burn-in is subcontracted to KESM
2. IWV is subcontracted to Oneida or Pernicka
3. Oneida is subcontracted as required for SEM
SECTION 2.11 CALIBRATION

GENERAL
The Calibration Laboratory functions are an integral part of the Quality Management System. Written procedures outlining the overall system and requirements for specific equipment calibration are maintained at each facility. All designated inspection, measuring, and test equipment used throughout the facility is identified and controlled in a known state of calibration.

CALIBRATION SYSTEM
Reference “Monitoring and measuring resources”, section 7.1.5 of REA’s Quality Manual.
SECTION 2.12 RETENTION OF QUALIFICATION

GENERAL
REA has defined internal process requirements to maintain qualification status once initial qualification has been completed. REA has established a set of criteria that is compiled to. Non-compliance to this set of criteria results in removal of product or process from the QML listing by DLA.

RETENTION OF QUALIFICATION SYSTEM

The specification defining the qualification retention requirements also defines and addresses the issues of QML line shutdown and QML removal.

The following is a list of reasons for removal from the QML listing by the Qualifying Agency:

- The QML product does not meet the quality, reliability or performance requirements of MIL-PRF-38535 and REA is unable to implement a corrective action plan as defined in this document.
- The QML microcircuit offered under contract does not meet the device procurement specification requirements.
- REA has terminated the QML technology which was qualified.
- REA requests its name and associated product be removed from the list.
- One or more of the conditions under which certification and qualification was granted have been violated.
- REA has failed to notify the qualifying activity of change in procedures, processes, etc., in accordance with the change control procedures of MIL-PRF-38535.
- REA’s name appears on the “Consolidated List of Debarred, Ineligible and Suspended Contractors”.
- REA has not complied with the requirement for retention of qualification, as stated in its internal specification.
- REA has failed to provide a certified statement, when QML microcircuits are supplied under contract for direct or indirect Government use, that such QML microcircuits have been tested to and met all the requirements of MIL-PRF-38535.

QUALITY SUPPORT DOCUMENTS

240111 QCI Qualification Procedures
SECTION 2.13 TRAINING

GENERAL
Training is a key element in the overall quality system. The system is designed to provide employees with the necessary skills and knowledge to perform tasks in a highly technical environment. The Training Department, Human Resources Department and the Manufacturing Department have the responsibility and authority to identify and implement effective training programs for all personnel.

Employee development training opportunities include, but are not limited to: financial support for advanced education and employee growth training through the corporate-wide center for training and development. Services are provided for technical and administrative training and development.

TRAINING
SECTION 2.14 CLEANLINESS AND ATMOSPHERIC CONTROLS

GENERAL
Specifications that define the cleanliness and atmospheric controls in a variety of process areas have been established in order to build product of the highest quality and reliability.

CLEANLINESS AND ATMOSPHERIC CONTROLS
Unique cleanliness and atmospheric controls are required to fabricate integrated circuits. REA has established a required set of specifications which define the requirements in the wafer fab and assembly areas. Clean room standards have been developed to minimize product contamination during processing. In addition, temperature and humidity limits are defined for critical process and storage areas and are monitored accordingly.

QUALITY SUPPORT DOCUMENTS
880035 Clean Room Procedures (Fab 59)
233151-T Test and QCI Environmental Control
233151-A QC Environmental Monitor Assembly
SECTION 2.15 ESD PROGRAM

GENERAL
In order to preclude ESD damage to product, REA has established an ESD program for handling product in all areas starting with die separation and through final product shipment including shipment to customers.

ESD PROGRAM
The REA ESD program was established using MIL-HDBK-263 and MIL-STD-1686 as a guide. The system, compliant to JESD625, includes all areas beginning with die separation and continuing through final product shipment including shipment to customers. Specifications have been generated which define the use of static-free work stations, the use of air ionization, ion guns and details of proper ESD handling, packaging and storage procedures. All applicable REA Manufacturing and Support personnel receive ESD training.

QUALITY SUPPORT DOCUMENTS

233403 ESD Procedures (Palm Bay)
SECTION 2.16 CERTIFICATION TEST PLAN

GENERAL

REA has manufacturing operations in Palm Bay, Florida and subcontracted services for production as stated. REA manufactures a large variety of QML parts using many technology flows. REA has transitioned parts into QML via the “Transitional QML” option and has obtained QML status for existing technologies. This section describes a general (non-technology specific) certification test plan for new technologies. Specific technology flow certification test plans will be written on an as required basis.

CERTIFICATION TEST PLAN

QML Certification Test Plan for New Products.
- Process/Product capability demonstration.
- REA Quality internal validation.
- Qualifying activity management and technology validation.
- Demonstration of manufacturing control of any offshore operations.

QML Certification Test Plan for New Technology
A formal certification test plan will be approved by the TRB for each technology flow to be certified. This plan will include:
- Milestone charts outlining the tests to be used to certify the processes.
- Tests to be accomplished on the TCV, SEC, PM, and TCI.
- For RHA parts, a RH evaluation plan

QUALITY SUPPORT DOCUMENTS
230415-QML RELIABILITY QUALIFICATION SPECIFICATION- QML
FIGURE 2.16.A
SECTION 2.17  QUALIFICATION TEST PLAN

GENERAL
REA manufactures a large variety of QML parts using many technology flows. REA has transitioned parts into QML via the “Transitional QML” option and has obtained QML status for existing technologies. This section describes a general (non-technology specific) certification test plan for new technologies. Specific technology flow certification test plans will be written on an as required basis.

QUALIFICATION TEST PLAN
A. Qualification Test Plan for New Products/Technologies
   In order to obtain QML qualification for a specific technology flow, the following requirements must be met:
   • Demonstration circuits will be designed and fabricated using the technology flow to be qualified.
   • SMD format specifications will be generated for the demonstration circuits.
   • The demonstration circuits will be assembled, tested, screened and submitted to qualification testing. See Figure 2.16.A.

B. Qualification Test Report for New Products/Technologies
   A qualification test plan and report will be generated and submitted to TRB for formal acceptance.

   This plan and subsequent report will typically include:
   • test flow
   • test limits
   • % test coverage
   • test sampling techniques
   • traceability records
   • technology flow
   • SMD format specifications for the determined demonstration vehicles
   • milestone charts

QUALITY SUPPORT DOCUMENTS
230415-QML  Reliability Qualification Specification – QML
230479  Technology Characterization Vehicles
   Section 3.3 of this document for additional information
SECTION 2.18 CORRECTIVE ACTION

GENERAL

The quality system provides an effective corrective action program which involves investigating the root cause of the problem and taking measures to prevent recurrence.

CORRECTIVE ACTION

Reference “Improvement”, section 10 of REA’s Quality manual.
SECTION 2.19 THIRD PARTY ACTIVITIES

GENERAL
REA exercises the option to use third party sources for product design, wafer foundry, assembly and test operations. The selected operation may be completed in part or in total by the third party.

THIRD PARTY
All third party suppliers are approved by an REA team to insure that an effective quality system has been implemented by the supplier. Standard operating procedures used by the supplier to generate the finished product/test will be assessed by REA personnel. Assessment tools may include but are not limited to a review of the process monitor program, physical assessment of the quality systems, and finished product evaluations.

Team members include applicable representatives from Quality, Reliability, Product, and Production Engineering. When the scope of the third party operation includes processes for QML material, required TRB members will review and approve the assessment plans and final data prior to product being processed for QML applications. The facility will be added to the QML plan.

REA personnel will generate a procurement specification for each third party supplier detailing the product/services and quality requirements necessary for compliance. All details of the specification will be negotiated and approved by the third party supplier and required REA personnel. Any major changes, as defined per 999004, will be presented to the applicable TRB for approval.

QUALITY SUPPORT DOCUMENTS

<table>
<thead>
<tr>
<th>Category</th>
<th>Document Name</th>
</tr>
</thead>
<tbody>
<tr>
<td>Procurement</td>
<td>Baseline Manufacturing Specification for Subcontractor (AMK)</td>
</tr>
<tr>
<td></td>
<td>Baseline Manufacturing Specification for Subcontractor (MMT)</td>
</tr>
<tr>
<td></td>
<td>General Quality and Reliability Requirements for Subcontractors</td>
</tr>
</tbody>
</table>
SECTION 3.0  QML TECHNOLOGY SPECIFIC

GENERAL

This section of the QM Plan provides a description of the following

- A database system used to control the internal specifications used to fabricate each part type of every technology.
- A list of critical process/product internal specifications
- Technology Grouping guidelines and list of QML technologies
SECTION 3.1 REA QML ELECTRONIC DATABASE SYSTEM

GENERAL

A listing of all the QML parts produced by REA can be found in the REA Electronic Database System. By using the database, reports can be generated to provide the following information for each part type:

- SMD Part Number
- REA marketing part number
- Product Description
- Die technology name/flow
- Process location (Design Center through Product Ship)
- Starting Substrate material procurement specification
- Base Wafer Mask Number
- Flow/Traveler numbers (Wafer Fab/Assembly/Test/QCI)
- Wafer Fab product parameter specification number (as applicable)
- Bonding diagram specification number
- Package procurement specification number
- Package code
- QCI traveler number

In addition, the Document Control electronic data base system (Intrepid) is capable of providing a listing of the required product flows, process travelers, material, inspection and testing documents, etc for each part number. Therefore the actual applicable specifications are not included in the QM Plan document.
SECTION 3.2  TECHNOLOGY FLOW

GENERAL

REA produces a multitude of QML parts from a wide variety of technologies. These parts are designed and manufactured in various locations throughout the world. For the purposes of this plan, a technology flow is defined as a manufacturing line which includes design, mask making, material fabrication, wafer fabrication, assembly/packaging and test. Each product family has a unique combination of the elements of a manufacturing line which form its “technology flow”.

REA TECHNOLOGY FLOWS

The technology flows for each of the REA QML product families can be found by accessing the Electronic Databases. Figure 3.2A provides a listing of the manufacturing/design locations that are used by REA to produce its QML products. Each technology flow is a unique combination of the various location/fabrication sites found in Figure 3.2A.
REA TECHNOLOGY GROUPING GUIDELINES

The following guidelines will be used to identify the appropriate technology grouping for each new product and identify the TCV, PM and SEC circuits within the group.

- Products must have the same isolation type
  - JI – junction isolation
  - DI – dielectric isolation
  - LOCOS – local oxide
  - REOX – recessed oxide
  - BW – bonded wafer oxide isolation
  - SOS – silicon on sapphire
- Have the same basic device structures and technology
  - NPN/PNP (Bipolar)
  - P and N channel FET’s (CMOS)
  - P/Nch FET’s and Bipolar NPN/PNPs (Bi-CMOS)
- Have the same basic layout ground rules
  - Minimum feature size
  - Same number of metal levels
- Have the similar application voltage
- Have the same gate material
  - Poly
  - Aluminum
- Have the same FAB location
  - FAB 59
  - UMC
  - TowerJazz
  - Global (IBM)
  - FAB 54 (Fab is inactive, Product is in a Die Bank)
  - FNDLY 4/5 (Fab is inactive, Product is in a Die Bank)
  - MITEL (Fab is inactive, Product is in a Die Bank)
- Must contain ½ the number of transistors of the largest die (for Digital)
- Represents the functionality of the process (for Analog)
- Has all the major circuit elements
- Fully functional circuit
- Product designed to the ground rules of the technology
- Can be tested for RAD Hard Assurance if required
- Has sufficient volume that it should be readily available for testing
- For a product to be selected the subteam must reached consensus that if the product yields and is reliable other products on the process will yield and be reliable.
- When the subteam has reached consensus on the product selection the product listing will be presented to the TRB for approval.
- Once approved by the TRB the table in Section 3.3 of the QM Plan that list the, PM’s & TCV’s by technology and fab will be formally changed through an ECN (Engineering Change Notice).
### QML QUALITY MANAGEMENT PLAN

<table>
<thead>
<tr>
<th></th>
<th>Renesas Palm Bay, Florida</th>
<th>Renesas New Jersey</th>
<th>Renesas RTP, N.C.</th>
<th>UMC Taiwan</th>
<th>TowerJazz California</th>
<th>Global (IBM) Vermont</th>
<th>Millennium Microtech Thailand</th>
<th>Amkor Philippines</th>
<th>Carsem Malaysia</th>
<th>Corwil CA.</th>
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</tbody>
</table>

**NOTE:** 1) NO DESIGN ACTIVE PRODUCT FOR QML IS CURRENTLY DESIGNED AT THE NORTH BRANCH FACILITY.

**FIGURE 3.2A**
### Section 3.3

#### General:
The following is a list of the PM’s & TCV’s by technology

**LIST OF PM’s & TCV’s**

<table>
<thead>
<tr>
<th>Die Technology</th>
<th>PM</th>
<th>TCV</th>
<th>FAB LOCATION</th>
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<td>HFHIB</td>
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<td>TA 11462</td>
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<td>MGDE</td>
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<td>LCMOS</td>
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<td>CMOS3AMT</td>
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<tr>
<td>SIGATE HVSIGATE</td>
<td>TA 03927&lt;br&gt;TA 3772&lt;br&gt;TA 50388</td>
<td>Transitioned Process (See Note 1)</td>
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<td>SAJI5/6</td>
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<td>L7</td>
<td>TA 03352M&lt;br&gt;TA 51122A</td>
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<td>TSOS4</td>
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<td>Transitioned Process (See Note 1)</td>
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<td>UHF</td>
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<td>AVLSI A1</td>
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<td>Transitioned Process (See Note 1)</td>
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### QML QUALITY MANAGEMENT PLAN

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<th>Die Technology</th>
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<td>51433</td>
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<td>HBC-10</td>
<td>TA51422J01</td>
<td>TA50550J01</td>
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<td>HPA2 60V,21 Mask 420747</td>
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<td>TA50728B</td>
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<td>TA51331A</td>
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<td>HVTDLM</td>
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<td>TA52228A</td>
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<td>UHF2/CMOS</td>
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<td>TA51843A</td>
<td>P59</td>
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<td>BiMOS-ESD</td>
<td>52520A</td>
<td>ICL3224</td>
<td>Fab 59</td>
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<td>TA53850A</td>
<td>Fab 59</td>
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<td>53141A</td>
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<td>P6SOI</td>
<td>N/A</td>
<td>54048C / D</td>
<td>TowerJazz</td>
</tr>
</tbody>
</table>

**Notes:**
1. Transitional Processes: Old technologies that have been transitioned to QML by REA do not have the QML tools such as Technology Characterization Vehicles (TCV's) and Standard Evaluation Circuit (SEC's), etc.; these technologies have years of QPL listing, extensive field history and compliant life test data to supplement the TCV and SEC data. Reliability data reports are generally available on the World Wide Web at: [Reliability Web Site](#).

2. During the qualification and subsequent production of the AVLSI-A1,-A1A, -A1R and -A1RA Wafer Fabrication processes at the Palm Bay manufacturing facility, the Metal 1 Molybdenum (Moly) exhibited a seam at certain steps traversing closely spaced Poly silicon lines. Reliability analysis of these seams, which included SEM analysis, Field Emission SEM analysis, Electromigration studies and Product Stress Testing,
showed no failures on representative samples exhibiting these seams. Based on these test results, the Moly seams will be inspected during SEM but will not be dispositioned based on the physical appearance of a seam. All other Mil-Std-883, Test Method 2018, SEM criteria as modified by this QM Plan (see Note in Figure 2.2.9.B) will apply. Reference Reliability Report: Reliability Special Report Covering Moly On AVLSI-A1, -A1A, -A1R & -A1RA Processes.

3 The AVLSI A1RF product periodically exhibits small reductions in Metal 1 width and Metal 1 depth caused by a wafer fabrication process anomaly. These reductions in Metal 1 dimensions can appear as a void during the assembly high power dice inspections. Reliability SEM analysis and current density analysis shows that void anomalies in Metal 1 that are \( \leq 50\% \) are acceptable even in an extreme event that the Metal 1 conductor and barrier metal are missing. The assembly inspection criteria will be modified in internal documentation to reflect accepting AVLSI A1RF material exhibiting a \( \leq 50\% \) Metal 1 line width reduction for voids as described herein.

4 Product technologies marked with an * are in the design and product qualification phase. Upon qualification completion and TRB approval product will be added to the QML product list and DLA certification listing.

5 Part overlooked when original list of transitional processes developed

6 Part and process added to support MMIII GRP.
SECTION 4.0 SITE QUALITY SYSTEMS MANUALS

The Quality Manual may be requested or may be accessed through the REA web page Quality Manuals and Procedures. The specification number for the manual is:

QOP-ISL-001 Quality Systems Manual
APPENDIX A

RADIATION HARDNESS ASSURANCE (RHA)

SCOPE
This appendix presents REA’s approach to RHA.

GENERAL
Microcircuits supplied to this document shall be manufactured and tested in accordance with REA approved baseline manufacturing flow and requirements herein.

DESIGN APPROACH
REA uses three methods in its design approach to satisfied new circuit requirement:

1. Design specifically for radiation hardness to the approved ground rules of the intended radiation hard wafer process.

2. Standard commercial designs built using a qualified process that is capable of producing circuits that meet the intended radiation requirements.

3. Product that is hardened by design, built using a qualified process that is capable of producing circuits that meet the intended radiation requirements.

MODEL AND DESIGN RULE VERIFICATIONS
Various methods and procedures were used in the portfolio of standard radiation hardened products being offered under this QM PLAN. These products were all designed or design verified to meet the intent of MIL-M-38510 and were designed released prior to the requirements of MIL-PRF-38535. New products developed after October 1, 1995 will follow requirements as outlined in MIL-PRF-38535.

WAFFER FABRICATION PROCESS CONTROLS AND PROCESS MONITOR
All radiation hardened products are produced on a specific radiation hardened wafer process or a process capable of meeting the radiation requirements as required (see radiation technology table B-1). The process specification/flows contain the details of each process and controls applicable to the specific process.

Each technology has a unique Process Monitor (PM) structure which is used for wafer acceptance and process control.
TECHNOLOGY CHARACTERIZATION
Selected product types from each technology were tested/characterized by REA, our customers or a government agency to the following radiation testing:
   a) Total Ionizing Radiation Dose (Condition A and Condition D)
   b) Dose Rate Upset
   c) Dose Rate Latch-up
   d) Neutron Irradiation
   e) Dose Rate Burn Out
   f) SEP including SEU, SEL, SEGR, SEDR, etc…, as required.

The specific radiation testing and specified limits for each Radiation Technology will be contained in the specific product Standard Microcircuit Drawing (SMD).

Upon product redesign, a process change, or a design rule change, that effects radiation performance as determined by the TRB retesting and characterization will be performed.

GROUP E TESTING
Total Ionizing Radiation Dose testing (Condition A and Condition D) is performed per MIL-STD-883, Method 1019 latest revision on every wafer with a minimum accept level of 2 (0).
TABLE A-1

<table>
<thead>
<tr>
<th>Die Technology</th>
<th>Technology Description</th>
<th>Product Family</th>
<th>Product Function</th>
<th>Process Design Active</th>
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<tbody>
<tr>
<td>MGR_CMOS</td>
<td>Metal Gate Radiation Hardened CMOS</td>
<td>CD4XXX</td>
<td>logic</td>
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<td>SOSLT</td>
<td>Silicon Gate Radiation Hardened SOS</td>
<td>HCS/HCTS</td>
<td>logic</td>
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<td>TSOS 4</td>
<td>Silicon Gate Radiation Hardened SOS</td>
<td>AcS/AcTS</td>
<td>logic</td>
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<td>TSOS 4</td>
<td>Silicon Gate Radiation Hardened SOS</td>
<td>HS6566XXXRH</td>
<td>64K Rams</td>
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<td>AcS/AcTS</td>
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<td>26cxxxRH</td>
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<td>Hardened Field Self Aligned JI CMOS</td>
<td>HS’80C86RH,82CXXRH</td>
<td>uP’S &amp; Peripherals</td>
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</table>
APPENDIX B

QML SHIP AHEAD OF QUALIFICATION TESTING (QCI/TCI) TO MEET CUSTOMER REQUIREMENTS

1.0 SCOPE

QML system for shipping QML product prior to QCI/TCI test completion.

NOTE: 1 This procedure is to be used in the event of hardships that would be incurred by the customer, by delaying shipments for qualification (QCI/TCI) test completion. The procedure may also be used with joint concurrence with the customer for other mutually agreed to situations.

2.0 REFERENCE DOCUMENTS

999032  SHIP AHEAD OF QUAL INSTRUCTIONS AND NON-STD

3.0 RESPONSIBILITIES and REQUIREMENTS

3.1 The Marketing Manager is responsible for completing and routing the Ship Ahead of Qualification approval form contained in specification 999032.

3.2 The following minimum information will be included on the Ship Ahead of Qualification request:
SMD part number and Date Code. The Date Code is only applicable to the form if the product is past the assembly seal operation.

Customer name and name of the customer contact making the request for Ship Ahead of Product QCI/TCI test results.

Reason for shipping ahead of qualification.

3.3 The initiator is responsible for routing the request to the following minimum for Material Review and Approval:
Marketing Manager
Production Control Manager
Contracts Administrator
Customer Engineering Manager
Test Area Quality Engineering (See para 3.4 for approval responsibility).
3.4 The Test Area Quality Engineering representative is responsible for:
Reviewing Product/Technology QCI/TCI history and supplying quantitative data of acceptance
history.
Contacting and obtaining approval from the responsible Product and Reliability Engineer.
Note: The Quality and Reliability engineers are typically members of the TRB board or use the TRB
respective member as a resource.

3.5 The Marketing representative is responsible for obtaining the signature of the REA Contract
Administrator, Marketing Manager, Quality Engineering and Customer Representative on the
agreement to accept product prior to QCI/TCI test completion. Reference specification 999032 for
forms.

3.6 The Marketing representative is responsible for providing Customer Engineering and the QML
Coordinator with a copy of the completed form and customer agreement letter.

3.7 Product will be shipped as a specific Custom Specific drawing number “R4573” specification.

3.8 The QML representative is responsible for submitting the completed request from to the CORE TRB.
Upon TRB review a copy of the information will be forwarded to the DLA office.

3.9 In the event of a QCI/TCI failure, the failure mode will be evaluated, the customer notified, and
product jeopardy evaluated jointly by the customer and REA personnel as defined in 240111 for
QCI/TCI failure disposition. Appropriate MRB disposition will be determined and the TRB notified.
The QML representative is responsible for notifying the DLA office.